

## Schottky Barrier Diode

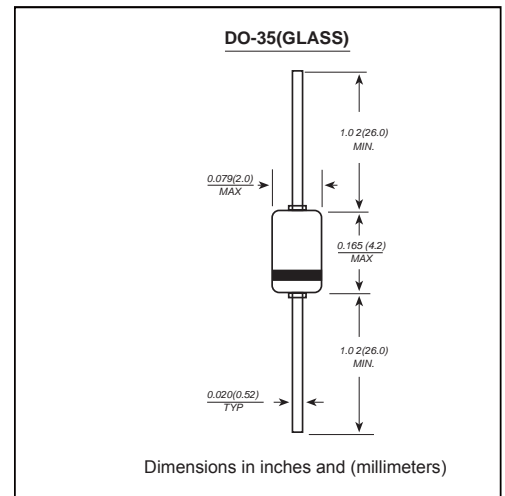
VOLTAGE RANGE: 30V PEAK PULSE POWER:200mW

### Features

- $V_R$  30V
- $I_{FM}$  300mA
- Applications where a very low forward voltage is required

### MECHANICAL DATA

- Case: DO-35
- Polarity: Color band denotes cathode end
- Mounting Position: Any



## MAXIMUM RATINGS AND CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified

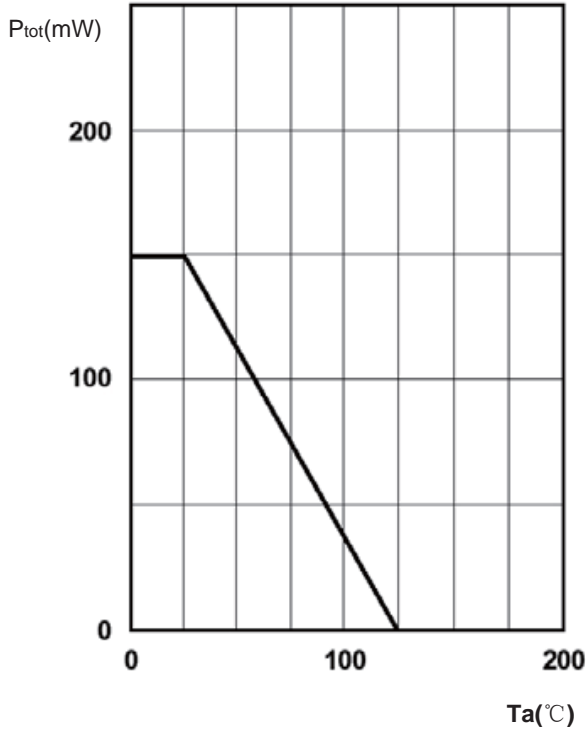
Item	Symbol	Unit	Conditions	Max
Continuous reverse voltage	$V_R$	V		30
Forward continuous current	$I_F$	mA	$T_a=25^\circ\text{C}$	200
Peak forward current	$I_{FM}$	mA	$T_a=25^\circ\text{C}$	300
Surge forward current	$I_{FSM}$	mA	$t_p \leq 1\text{s}, T_a=25^\circ\text{C}$	600
Power dissipation	$P_{tot}$	mW	$T_a=65^\circ\text{C}$	200
Maximum junction temperature	$T_j$	°C		125
Ambient operating temperature range	$T_A$			-65 to +125
Storage temperature range	$T_{stg}$	°C		-65 to +150
Junction ambient	$R_{thJA}$	°C/W	On PC board 50mm×50mm×1.6mm	250

## Electrical Specification ( $T_A=25^\circ\text{C}$ unless otherwise specified)

Item	Symbol	Unit	Conditions	Min	Max
Reverse breakdown voltage	$V_{(BR)R}$	V	$I_R=10\mu\text{A}$ (pulsed)	30	
Leakage current	$I_R$	$\mu\text{A}$	$V_R=25\text{V}$		2
Forward voltage pulse test $t_p < 300\mu\text{s}, s < 2\%$	VF	V	$I_F=0.1\text{mA}$		0.24
		V	$I_F=1\text{mA}$		0.32
		V	$I_F=10\text{mA}$		0.4
		V	$I_F=30\text{mA}$		0.5
		V	$I_F=100\text{mA}$		0.8
Capacitance	$C_{tot}$	pF	$V_R=1\text{V}, f=1\text{MHz}$		10
Reverse recovery time	$t_{rr}$	ns	$I_F=I_R=10\text{mA}, I_R=0.1\text{mA}$		5

# RATINGS AND CHARACTERISTIC CURVES

Fig1. Admissible power dissipation vs.ambient temperature



characteristics

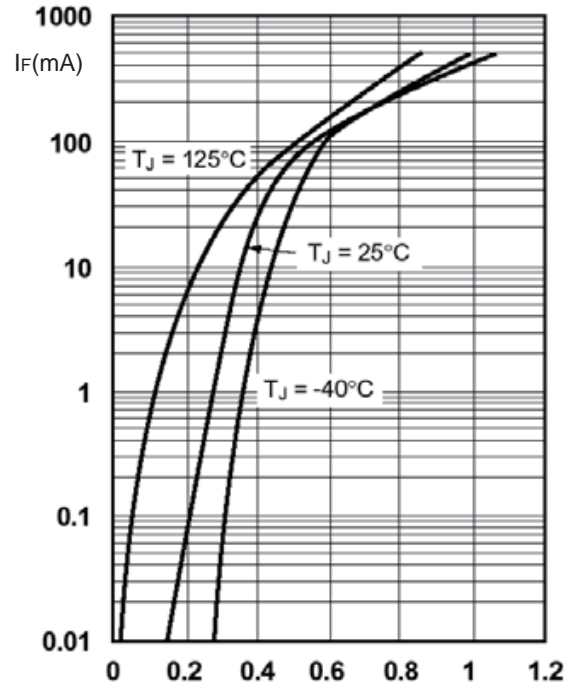


Fig3. Typical reverse characteristics

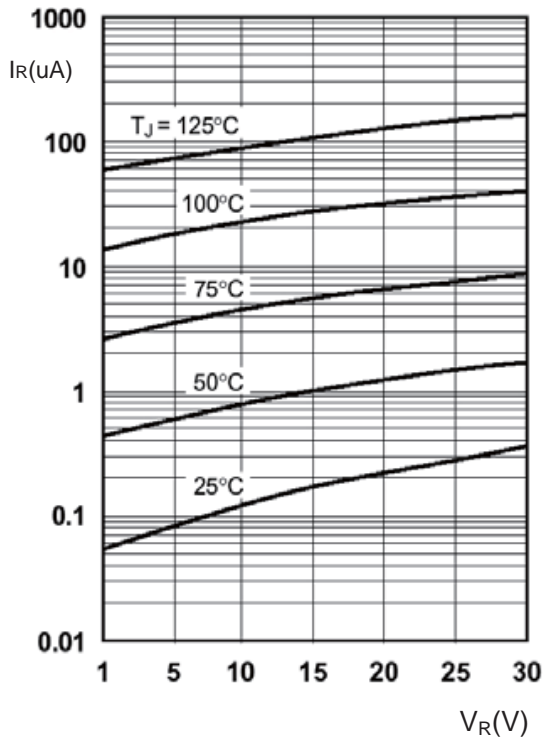


Fig4. Typical junction capacitance

